

Features

- Uses PingWei advanced PerfectMOS6 technology
- Extremely low on-resistance $R_{DS(on)}$
- Excellent $Q_g \times R_{DS(on)}$ product(FOM)
- Excellent Low Ciss
- Qualified according to JEDEC criteria



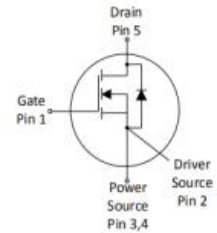
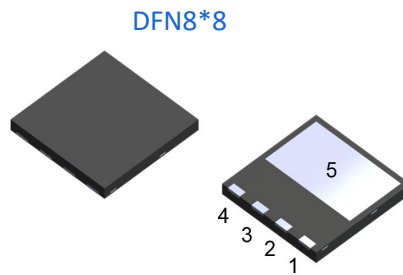
100% DVDS Tested
100% Avalanche Tested

Applications

- PFC stages, hard switching PWM stages and resonant switching
- PWM stages for e.g. PC Silverbox, Adapter, LCD & PDP TV, Lighting, Server, Telecom and UPS

Product Summary

V_{DS}	650V
$R_{DS(on)}@10V$ typ	150mΩ
I_D	20A



Package Marking and Ordering Information

Part #	Marking	Package	Packing	Reel Size	Tape Width	Qty
PWE180N65WS	PWE180N65WS	DFN8*8	Tape&Reel	13 inches	16mm	4000pcs

Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Drain-source voltage	V_{DS}	650	V
Continuous drain current	I_D	20	A
$T_C = 25^\circ\text{C}$ (Silicon limit)		13	
$T_C = 100^\circ\text{C}$ (Silicon limit)			
Pulsed drain current ($T_C = 25^\circ\text{C}$, $t_p = 100\mu\text{s}$)	$I_{D\ pulse}$	80	A
Avalanche energy, single pulse ($L=10\text{mH}$, $V_{ds}=50\text{V}$)	E_{AS}	195	mJ
Gate-Source voltage	V_{GS}	± 20	V
Power dissipation	P_{tot}	125	W
$T_C = 25^\circ\text{C}$		0.9	
$T_a = 25^\circ\text{C}$			
Operating junction and storage temperature	T_j, T_{stg}	-55...+150	$^\circ\text{C}$
Soldering temperature, wave soldering only allowed at leads (1.6mm from case for 10s)	T_{sold}	260	$^\circ\text{C}$



Thermal Resistance

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Thermal resistance, junction – case.	RthJC	-	-	1.0	°C/W	-
Thermal resistance, junction - ambient(min. footprint)	RthJA	-	-	132	°C/W	-

Electrical Characteristic (at Tj = 25 °C, unless otherwise specified)

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		

Static Characteristic

Drain-source breakdown voltage	BV_{DSS}	650	-	-	V	$V_{GS}=0V, I_D=250\mu A$
Gate threshold voltage	$V_{GS(th)}$	2	-	4	V	$V_{DS}=V_{GS}, I_D=250\mu A$
Zero gate voltage drain current	I_{DSS}	-	0.04	1	μA	$V_{DS}=650V, V_{GS}=0V$ $T_j=25^\circ C$ $T_j=150^\circ C$
Gate-source leakage current	I_{GSS}	-	± 10	± 100	nA	$V_{GS}=\pm 20V, V_{DS}=0V$
Drain-source on-state resistance	$R_{DS(on)}$	-	150	180	mΩ	$V_{GS}=10V, I_D=10A$
Transconductance	g_{fs}	-	12	-	S	$V_{DS}=5V, I_D=10A$

Dynamic Characteristic

Input Capacitance	C_{iss}	-	1625	-	pF	$V_{GS}=0V, V_{DS}=400V,$ $f=1MHz$
Output Capacitance	C_{oss}	-	52	-		
Reverse Transfer Capacitance	C_{rss}	-	43	-		
Gate Total Charge	Q_G	-	42	-	nC	$V_{DS}=520V, I_D=20A,$ $V_{GS}=10V$
Gate-Source charge	Q_{gs}	-	11	-		
Gate-Drain charge	Q_{gd}	-	18	-		
Turn-on delay time	$t_{d(on)}$	-	30	-	ns	$V_{GS}=10V, V_{DD}=325V,$ $R_{G_ext}=10\Omega, I_D=3.6A$
Rise time	t_r	-	40	-		
Turn-off delay time	$t_{d(off)}$	-	50	-		
Fall time	t_f	-	25	-		
Gate resistance	R_G	-	10	-	Ω	$V_{GS}=0V, V_{DS}=0V,$ $f=1MHz$



Body Diode Characteristic

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Body Diode Forward Voltage	V_{SD}	-	0.83	1.5	V	$V_{GS}=0V, I_{SD}=10A$
Body Diode Continuous Forward Current	I_S	-	-	20	A	$TC = 25^{\circ}C$
Body Diode Pulsed Current	I_S pulse	-	-	81	A	$TC = 25^{\circ}C$
Body Diode Reverse Recovery Time	t_{rr}	-	256	-	ns	$I_F=1A, dI/dt=100A/\mu s$
Body Diode Reverse Recovery Charge	Q_{rr}	-	2542	-	nC	



Typical Performance Characteristics

Fig 1: Output Characteristics

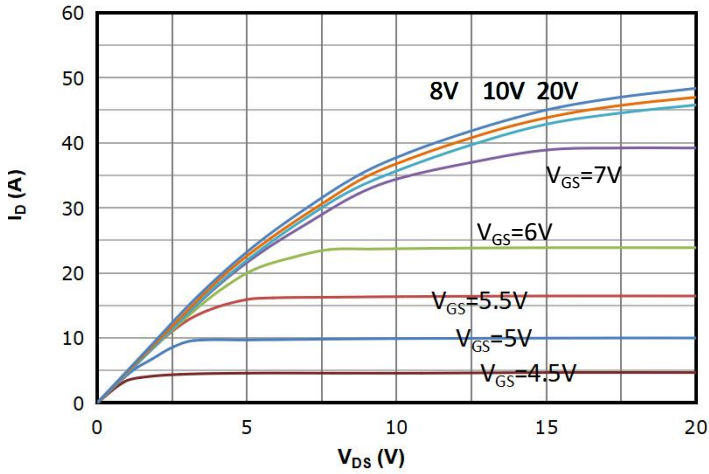


Fig 2: Transfer Characteristics

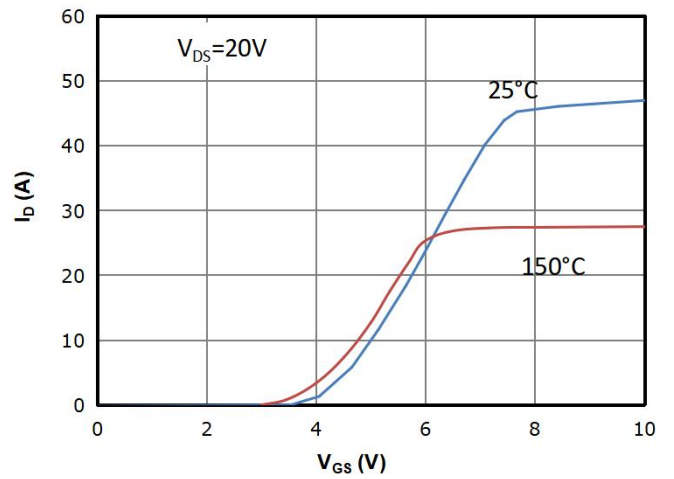


Fig 3: $R_{DS(on)}$ vs Drain Current and Gate Voltage

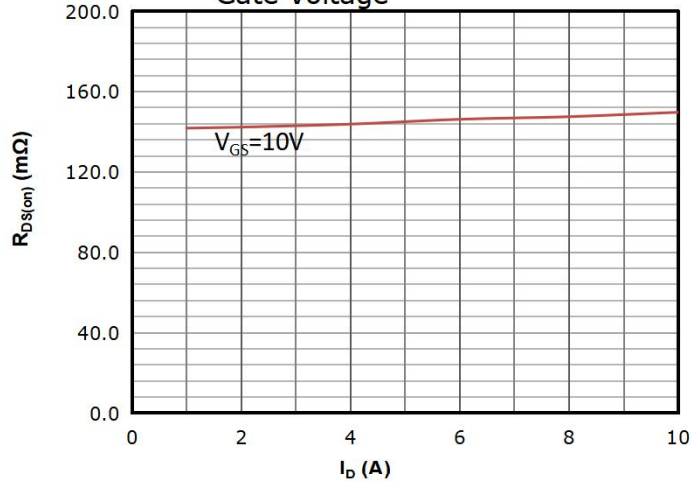


Fig 4: $R_{DS(on)}$ vs Gate Voltage

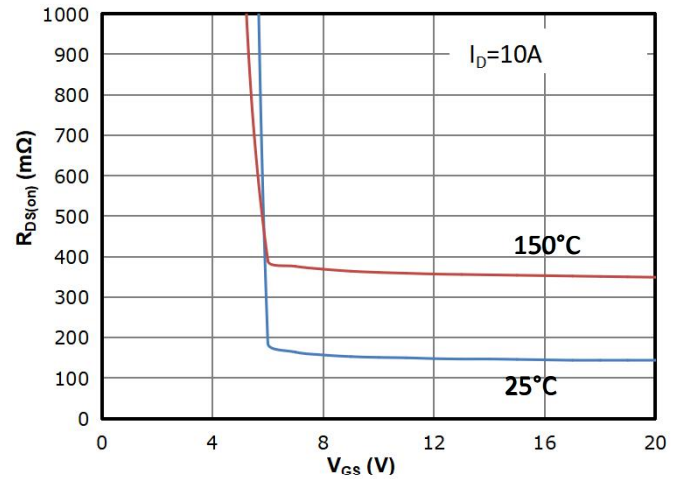


Fig 5: $R_{DS(on)}$ vs. Temperature

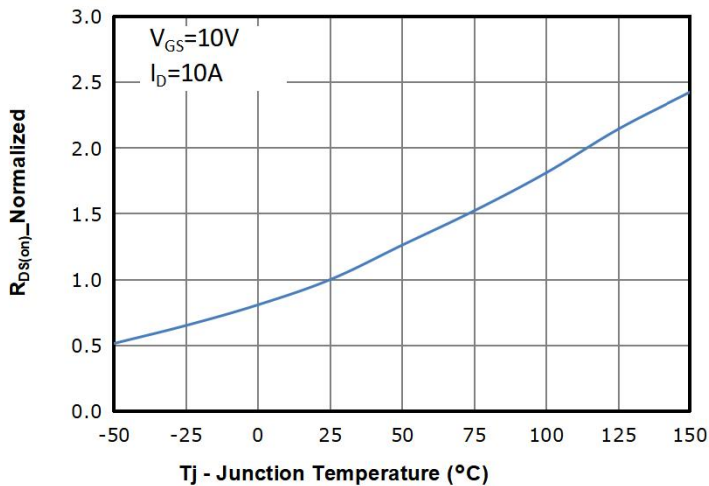


Fig 6: $V_{GS(th)}$ vs. Temperature

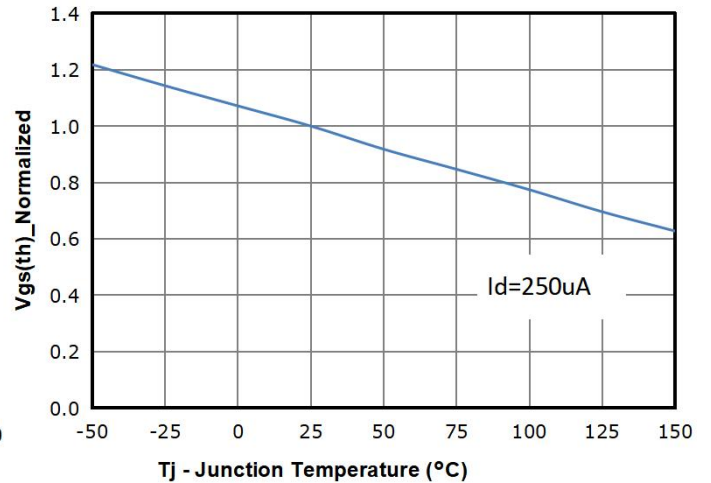




Fig 7: BVdss vs. Temperature

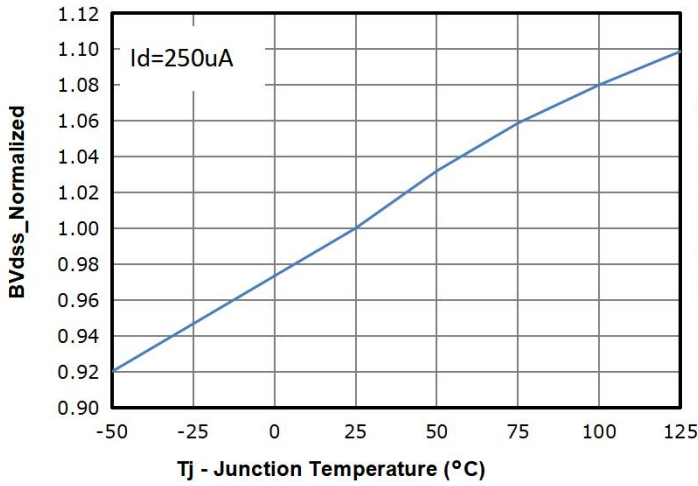


Fig 8: Capacitance Characteristics

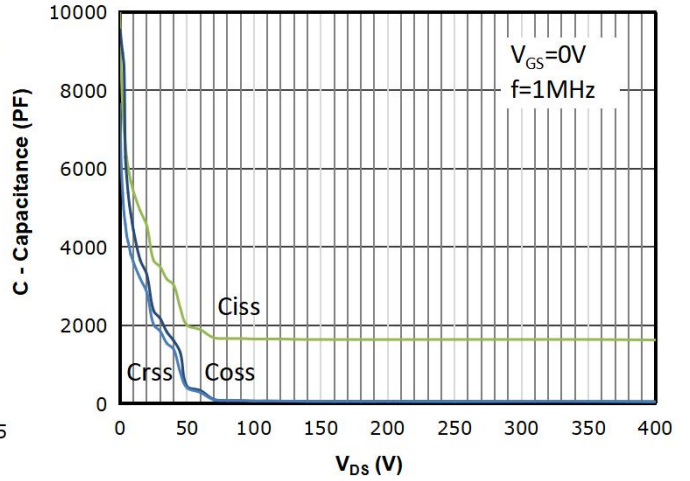


Fig 9: Gate Charge Characteristics

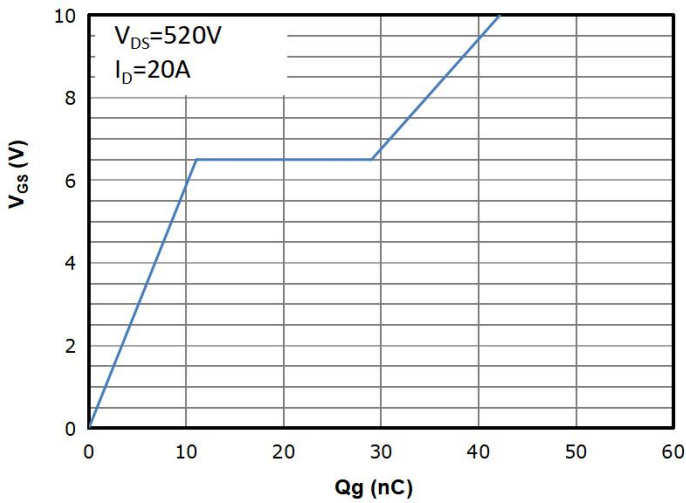


Fig 10: Body-diode Forward Characteristics

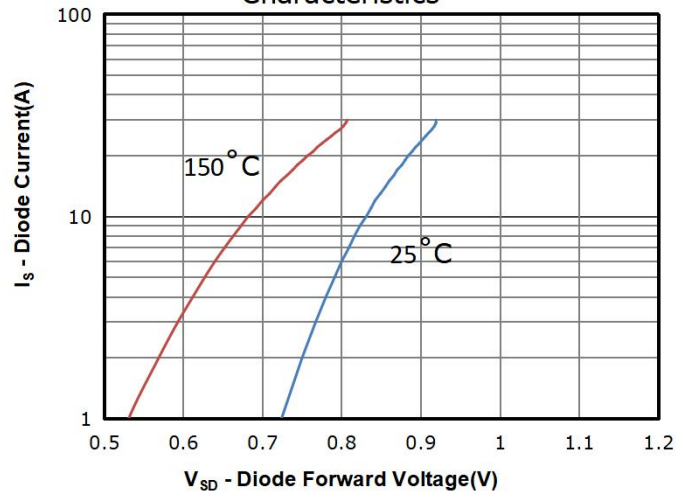


Fig 11: Power Dissipation

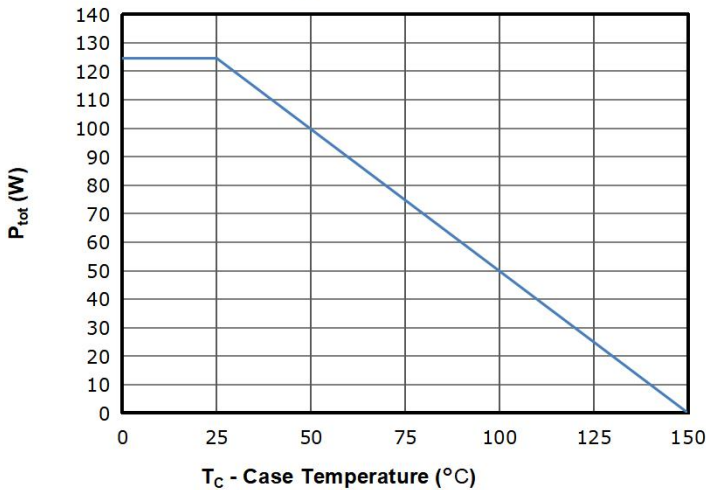


Fig 12: Drain Current Derating

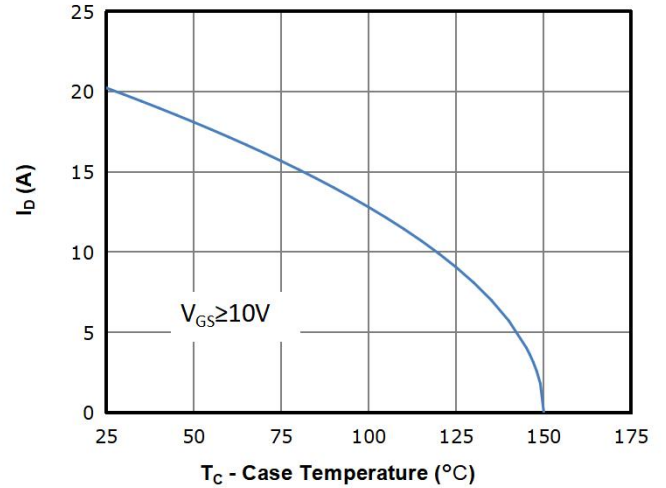




Fig 13: Safe Operating Area

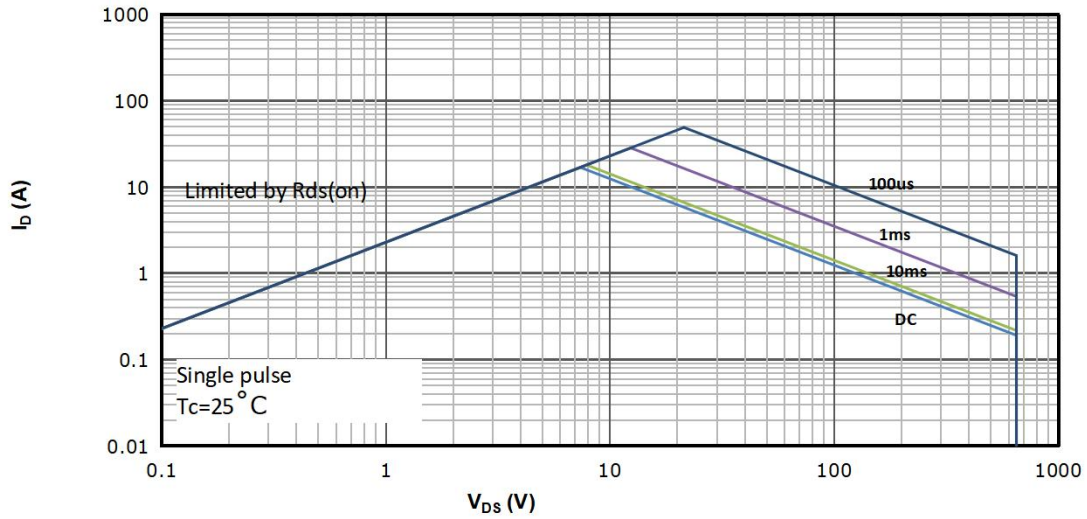
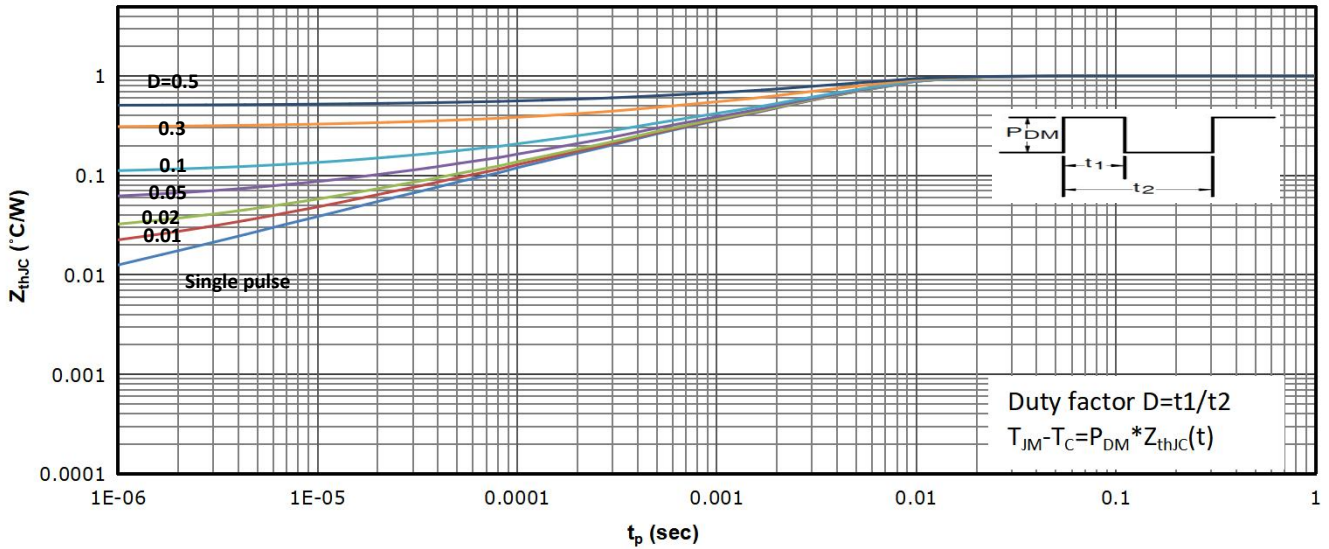
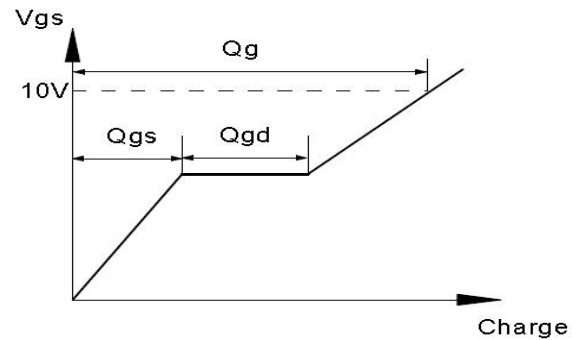
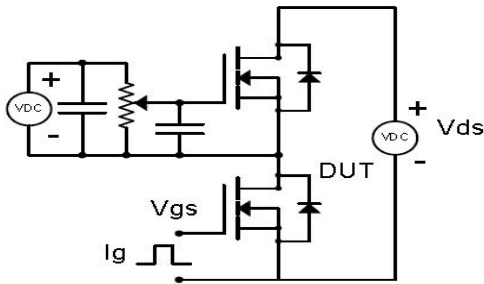


Fig 14: Max. Transient Thermal Impedance

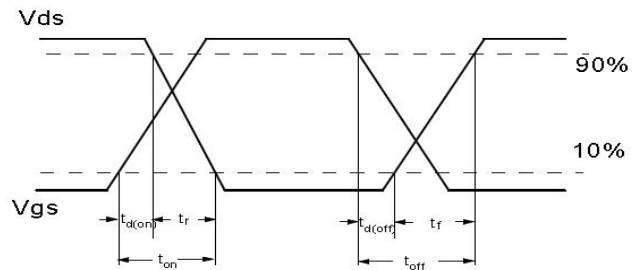
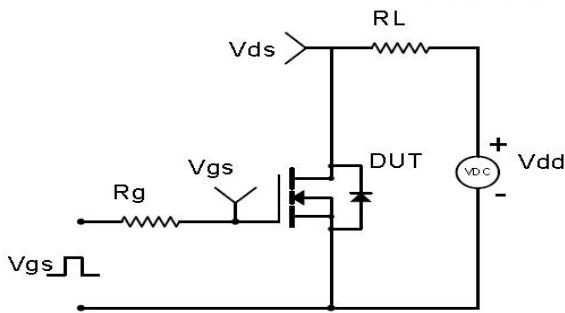


Test Circuit & Waveform

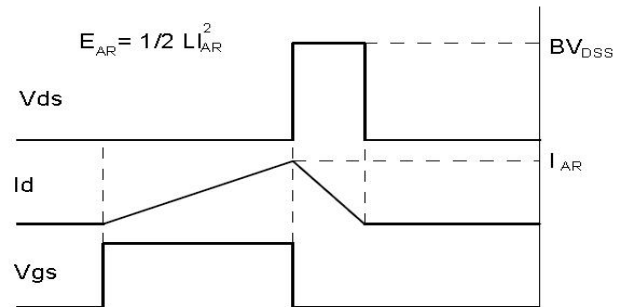
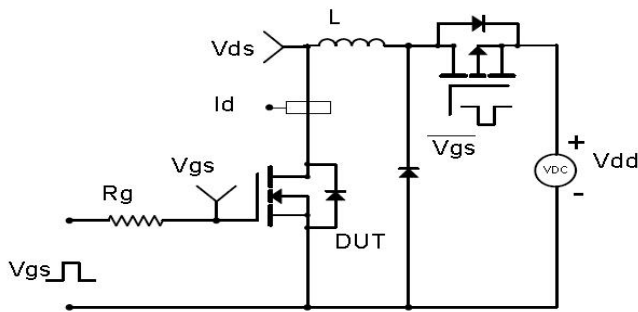
Gate Charge Test Circuit & Waveform



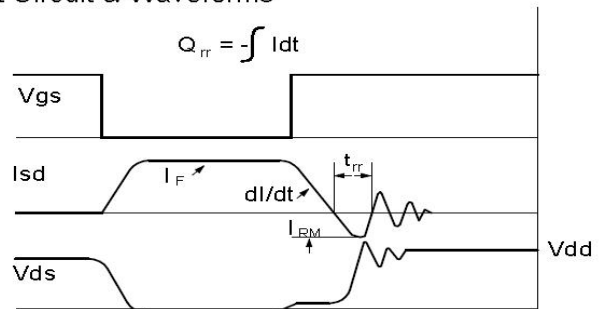
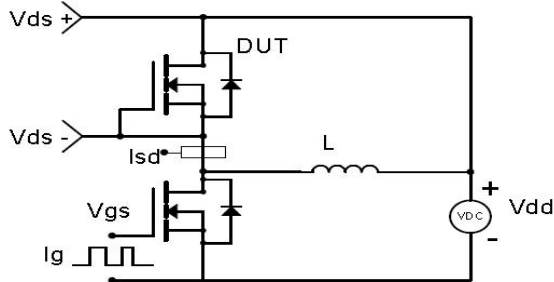
Resistive Switching Test Circuit & Waveforms



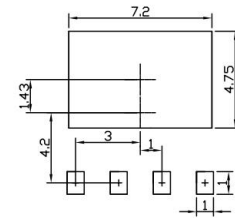
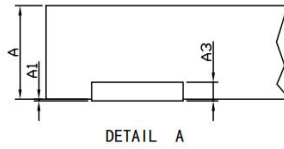
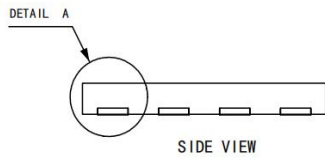
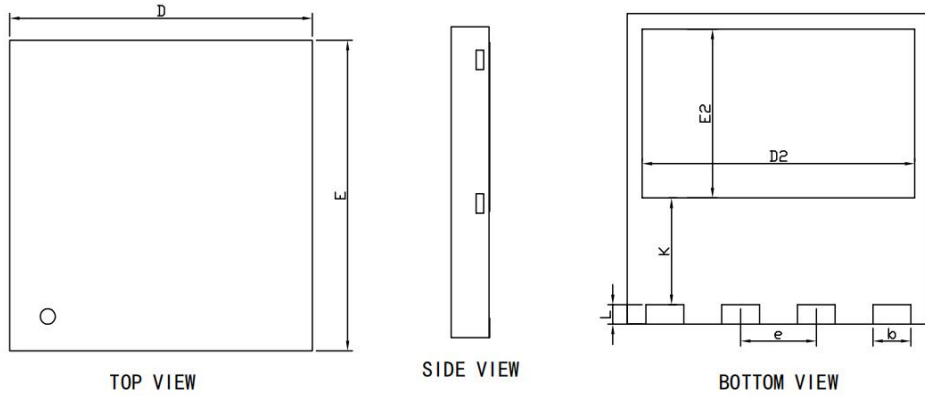
Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



Package Outline: DFN8*8



RECOMMENDED LAND PATTERN

UNIT: mm

SYMBOL	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.90	1.10	0.035	0.043
A1	0.00	0.05	0.000	0.002
A3	0.20		0.008	
b	0.90	1.10	0.035	0.043
D	7.90	8.10	0.311	0.319
E	7.90	8.10	0.311	0.319
D2	7.10	7.30	0.280	0.287
E2	4.25	4.45	0.167	0.175
e	1.90	2.10	0.075	0.083
K	2.65	2.85	0.104	0.112
L	0.40	0.60	0.016	0.024



Revision History

Revision	Date	Major changes
1.0	2022/9/5	Release of Formal Version.

Disclaimer

Any and all semiconductor products have certain probability to fail or malfunction, which may result in personal injury, death or property damage. Customer are solely responsible for providing adequate safe measures when design their systems.

Unless otherwise specified in the datasheet, the product is designed and qualified as a standard commercial product and is not intended for use in applications that require extraordinary levels of quality and reliability, such as automotive, aviation/aerospace and life-support devices or systems.

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